

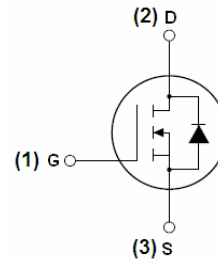
FNK N-Channel Enhancement Mode Power MOSFET

Description

The FNK03N06E uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

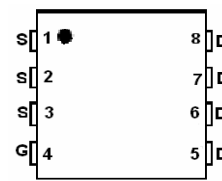
General Features

- $V_{DS} = 30V, I_D = 90A$
 $R_{DS(ON)} < 5.9m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 7.5m\Omega @ V_{GS} = 5V$



Schematic diagram

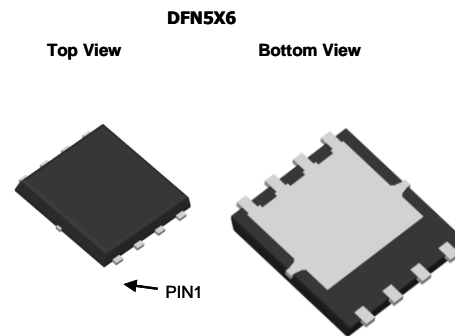
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation



Marking and pin assignment

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| FNK03N06E | FNK03N06E | DFN5*6-8L | - | - | - |

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|---------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 90 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_D (100^\circ C)$ | 50 | A |
| Pulsed Drain Current | I_{DM} | 360 | A |
| Maximum Power Dissipation | P_D | 107 | W |
| Derating factor | | 0.56 | W/ $^\circ C$ |
| Single pulse avalanche energy (Note 5) | E_{AS} | 150 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--|-----------------|-----|------|
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JC}$ | 1.4 | °C/W |
|--|-----------------|-----|------|

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

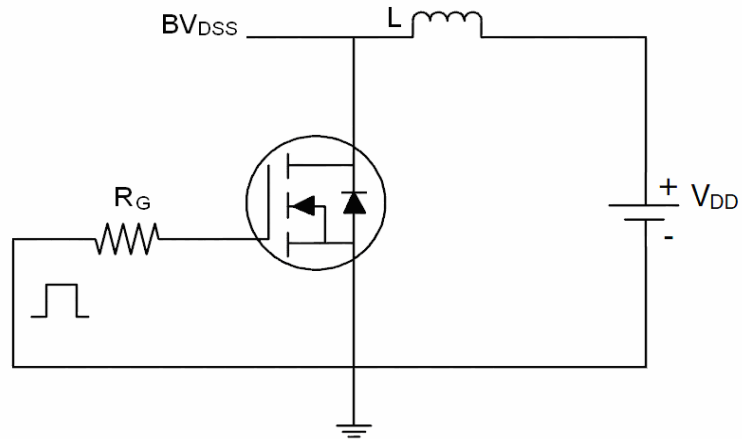
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---------------------|---|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 30 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V, V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics ^(Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1 | 1.2 | 1.7 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =10A | - | 4.1 | 5.9 | mΩ |
| | | V _{GS} =5V, I _D =4.5A | - | 5.0 | 7.5 | |
| Forward Transconductance | g _{FS} | V _{DS} =5V, I _D =24A | 20 | - | - | S |
| Dynamic Characteristics ^(Note4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =15V, V _{GS} =0V, F=1.0MHz | - | 2060 | - | PF |
| Output Capacitance | C _{oss} | | - | 320 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 235 | - | PF |
| Switching Characteristics ^(Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =10V, I _D =30A V _{GS} =10V, R _{GEN} =2.7Ω | - | 20 | - | nS |
| Turn-on Rise Time | t _r | | - | 15 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 60 | - | nS |
| Turn-Off Fall Time | t _f | | - | 10 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =10V, I _D =30A, V _{GS} =10V | - | 51 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 14 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 11 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage ^(Note 3) | V _{SD} | V _{GS} =0V, I _S =24A | - | - | 1.2 | V |
| Diode Forward Current ^(Note 2) | I _S | | - | - | 80 | A |
| Reverse Recovery Time | t _{rr} | TJ = 25°C, IF = 80A | - | 32 | 50 | nS |
| Reverse Recovery Charge | Q _{rr} | di/dt = 100A/μs ^(Note3) | - | 12 | 20 | nC |

Notes:

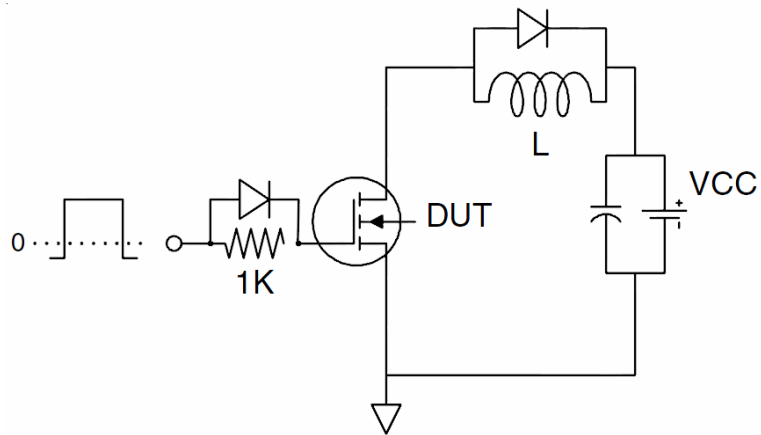
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, L=1mH, R_g=25\Omega$

Test Circuit

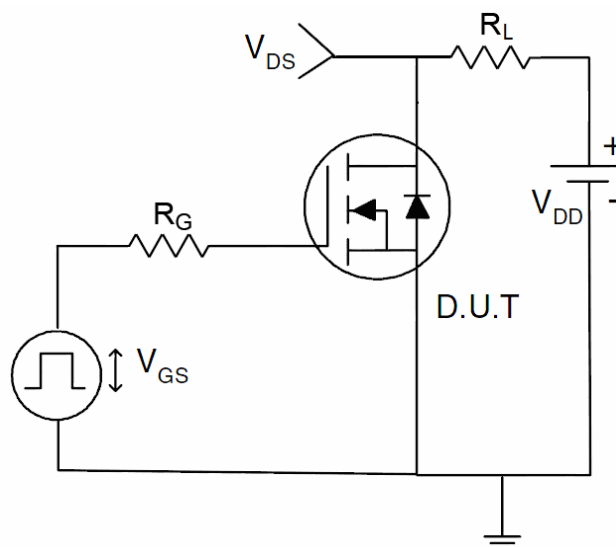
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

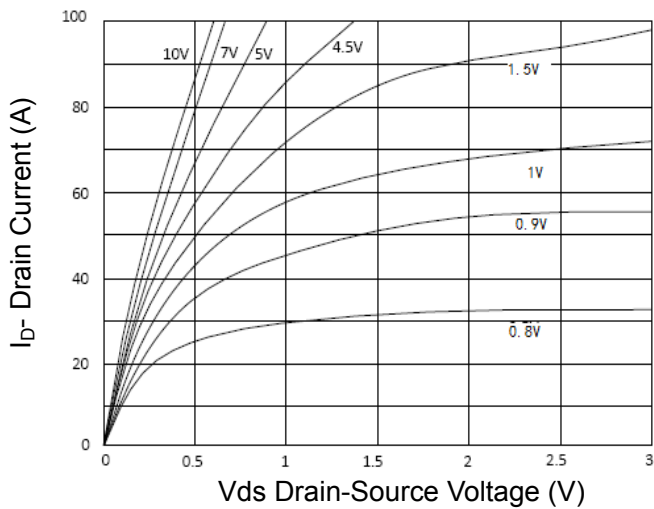


Figure 1 Output Characteristics

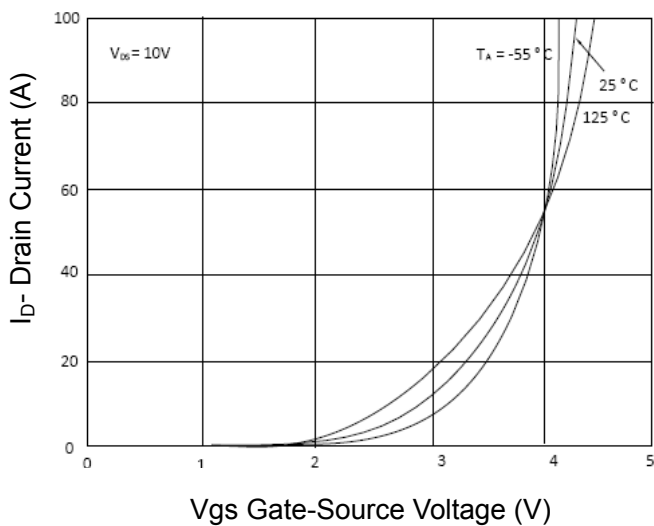


Figure 2 Transfer Characteristics

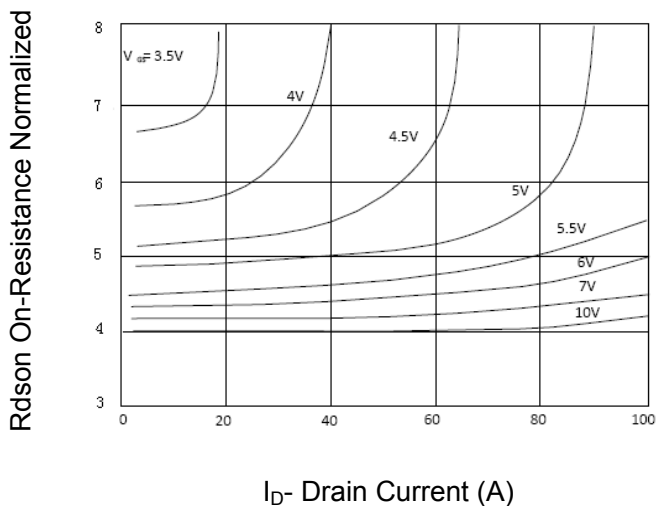


Figure 3 Rdson- Drain Current

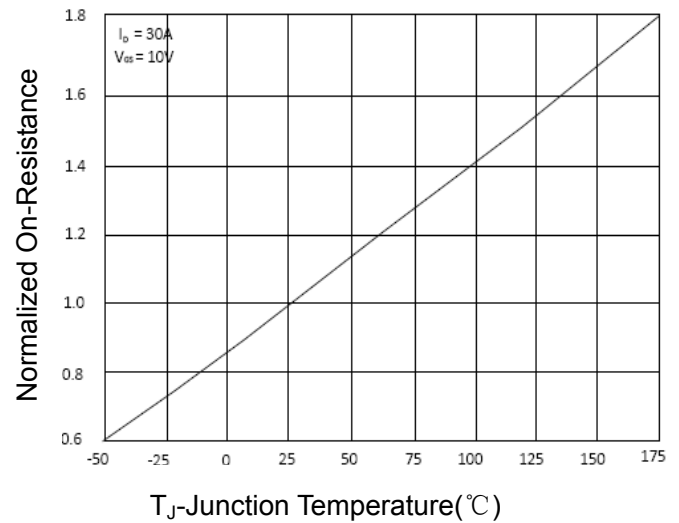


Figure 4 Rdson-Junction Temperature

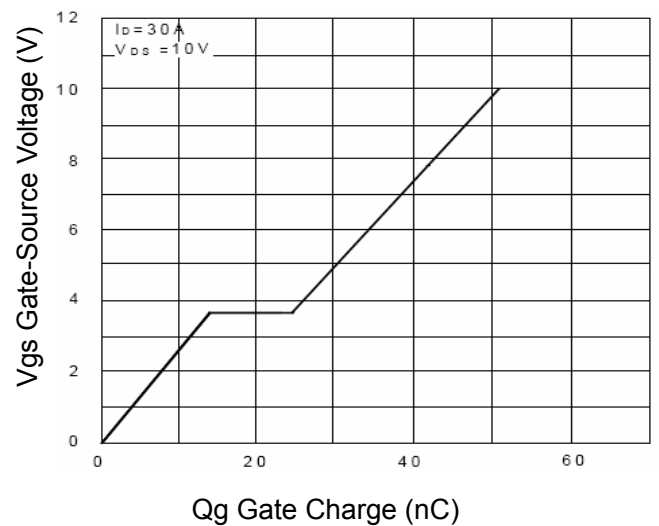


Figure 5 Gate Charge

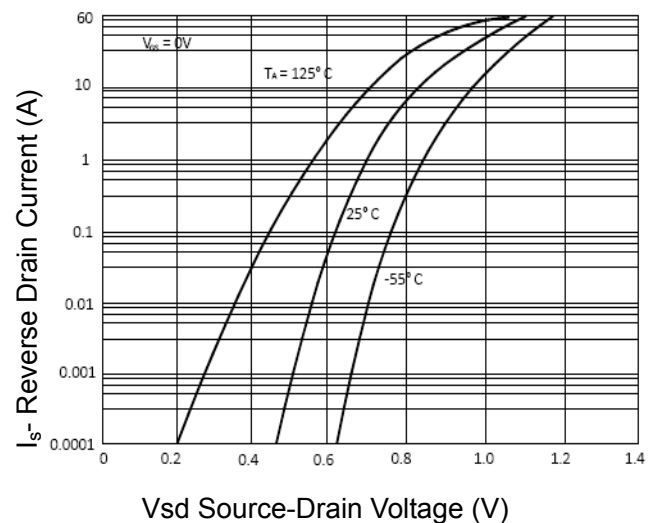


Figure 6 Source- Drain Diode Forward

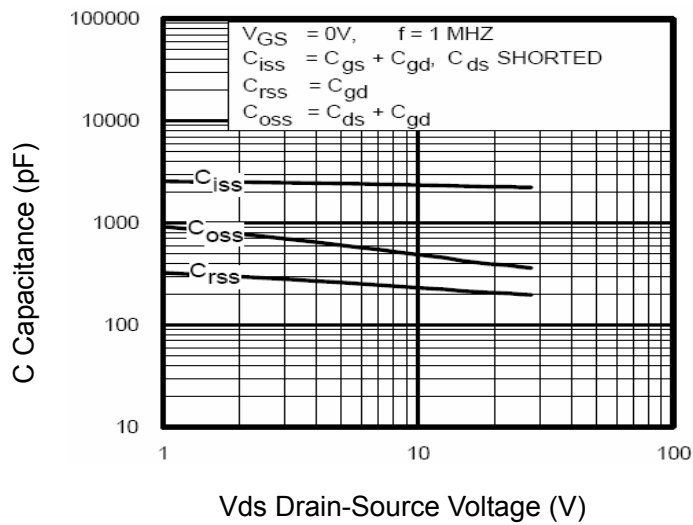


Figure 7 Capacitance vs Vds

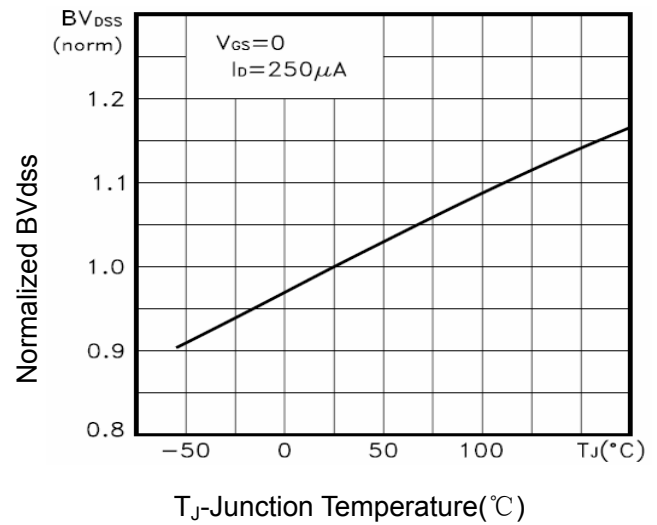


Figure 9 BV_{DSS} vs Junction Temperature

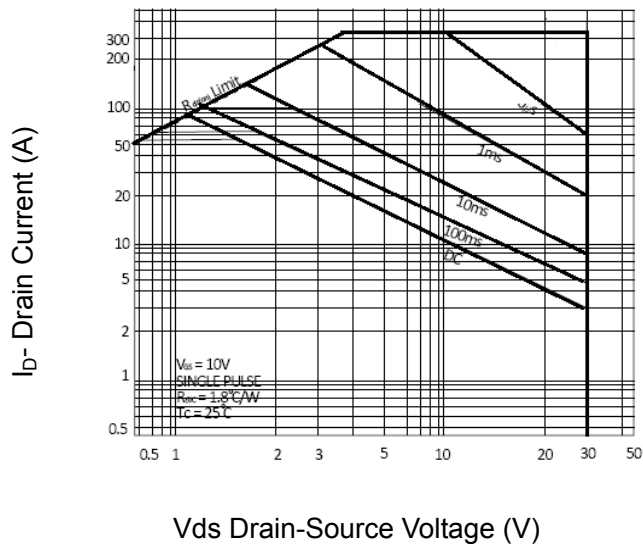


Figure 8 Safe Operation Area

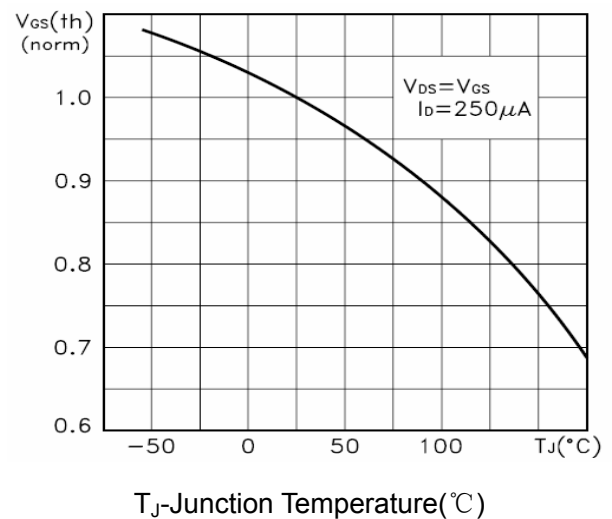


Figure 10 $V_{GS(th)}$ vs Junction Temperature

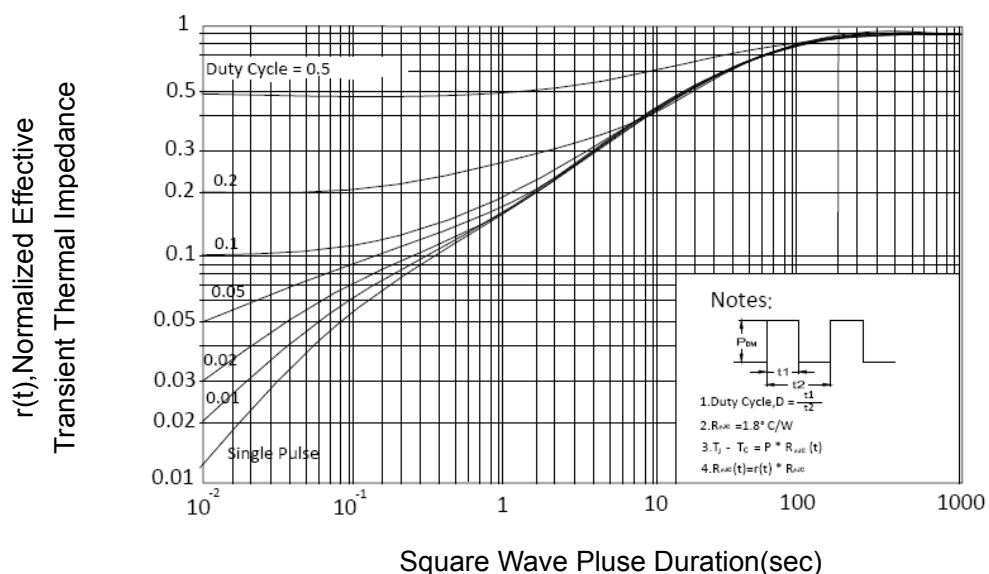
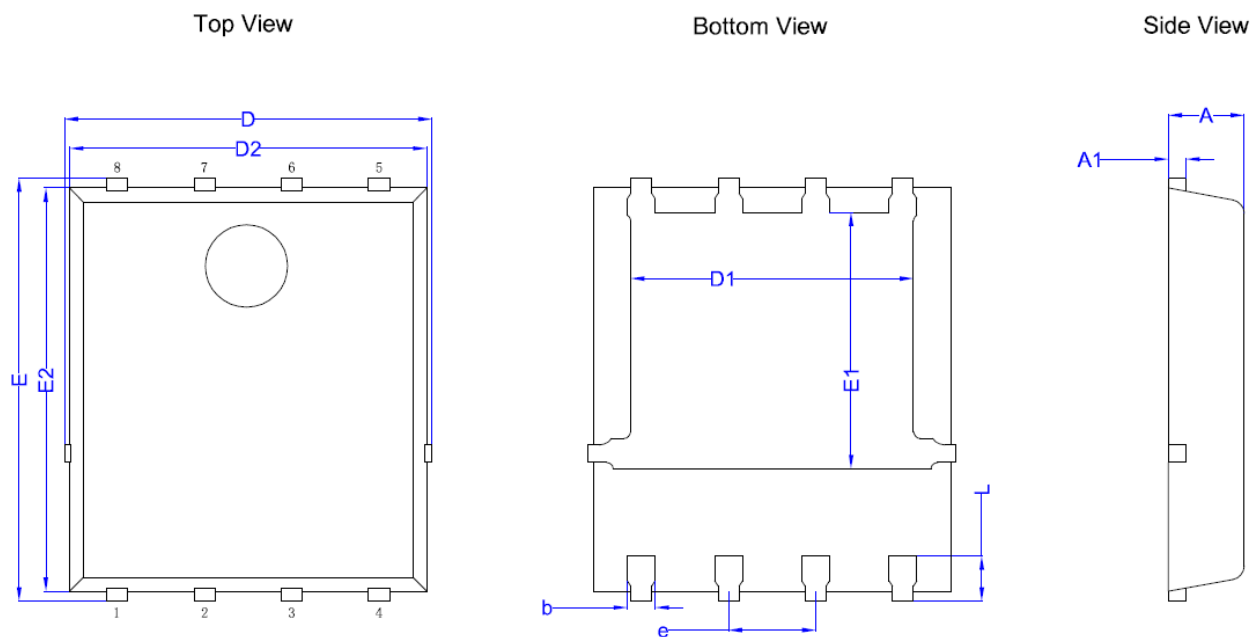


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



| SYMBOL | MILLIMETER | | |
|--------|------------|------|------|
| | MIN | NOM | MAX |
| A | 1.00 | 1.10 | 1.20 |
| A1 | 0.254 BSC | | |
| D | 5.15 | 5.35 | 5.55 |
| E | 5.95 | 6.15 | 6.35 |
| D1 | 3.92 | 4.12 | 4.32 |
| E1 | 3.52 | 3.72 | 3.92 |
| D2 | 5.00 | 5.20 | 5.40 |
| E2 | 5.66 | 5.86 | 6.06 |
| e | 1.27BSC | | |
| b | 0.31 | 0.41 | 0.51 |
| L | 0.56 | 0.66 | 0.76 |

ATTENTION:

- FNK reserves the right to make changes to the information herein for the improvement of the design and performance without further notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- FNK assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all FNK products described or contained herein.
- Specifications of any and all FNK products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- FNK strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all FNK products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the FNK product that you intend to use.
- FNK will supply the best possible product for customers!